Elektronische Bauelemente

SID40N03

36A, 30V, $R_{DS(ON)}$ 21mΩ

N-Channel Enhancement Mode Power Mos.FET

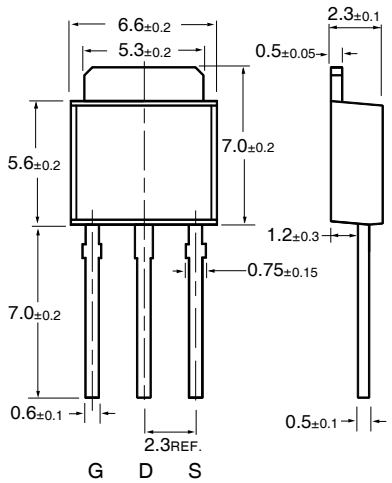
RoHS Compliant Product

Description

The SID40N03 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-251 is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

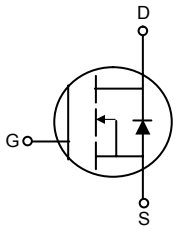
TO-251



Dimensions in millimeters

Features

* Repetitive Avalanche Rated
* Dynamic dv/dt Rating
* Simple Drive Requirement
* Fast Switching



Marking Code: 40N03
XXXX(Date Code)

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, V_{GS}@10V	I_D@T_C=25°C	36	A
Continuous Drain Current, V_{GS}@10V	I_D@T_C=100°C	25	A
Pulsed Drain Current[1]	I_{DM}	150	A
Total Power Dissipation	P_D@T_C=25°C	50	W
Linear Derating Factor		0.4	W/°C
Operating Junction and Storage Temperature Range	Tj, Tstg	-55~+150	°C

Thermal Data

Parameter		Symbol	Ratings	Unit
Thermal Resistance Junction-case	Max.	Rthj-c	2.5	°C /W
Thermal Resistance Junction-ambient	Max.	Rthj-a	110	°C/W

Electrical Characteristics(Tj=25°C Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	BV_{DSS}	30	–	–	V	V_{GS}=0V, I_D=250uA
Breakdown Voltage Temp. Coefficient	$\triangle BV_{DS}/\triangle Tj$	–	0.037	–	V/°C	Reference to 25°C, I_D=1mA
Gate Threshold Voltage	$V_{GS(th)}$	1.0	–	3.0	V	V_{DS}=V_{GS}, I_D=250uA
Gate-Source Leakage Current	I_{GSS}	–	–	±100	nA	V_{GS}=±20V
Drain-Source Leakage Current (Tj=25°C)	I_{DSS}	–	–	25	uA	V_{DS}=30V,V_{GS}=0
Drain-Source Leakage Current(Tj=150°C)		–	–	250	uA	V_{DS}=24V,V_{GS}=0
Static Drain-Source On-Resistance	$R_{DS(ON)}$	–	18	21	mΩ	V_{GS}=10V, I_D=18A
		–	24	30		V_{GS}=4.5V, I_D=14A
Total Gate Charge[2]	Qg	–	17	–	nC	I_D=18A V_{DS}=24V V_{GS}= 5V
Gate-Source Charge	Qgs	–	3	–		
Gate-Drain ("Miller") Charge	Qgd	–	10	–		
Turn-on Delay Time[2]	$T_{d(ON)}$	–	7.2	–	nS	V_{DD}=15V I_D=18A V_{GS}=10V R_G=3.3Ω R_D=0.83Ω
Rise Time	Tr	–	60	–		
Turn-off Delay Time	$T_{d(Off)}$	–	22.5	–		
Fall Time	T_f	–	10	–		
Input Capacitance	Ciss	–	800	–	pF	V_{GS}=0V V_{DS}=25V f=1.0MHz
Output Capacitance	Coss	–	380	–		
Reverse Transfer Capacitance	Crss	–	133	–		
Forward Transconductance	Gfs	–	26	–	S	V_{DS}=10V, I_D=18A

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Forward On Voltage[2]	V_{SD}	–	–	1.3	V	I_S=36 A, V_{GS}=0V.Tj=25°C
Continuous Source Current(Body Diode)	I_S	–	–	36	A	V_D=V_G=0V,V_S=1.3 V
Pulsed Source Current(Body Diode)[1]	I_{SM}	–	–	150	A	

Notes: 1.Pulse width limited by safe operating area.
2.Pulse width≦300us, dutycycle≦2%.

Characteristics Curve

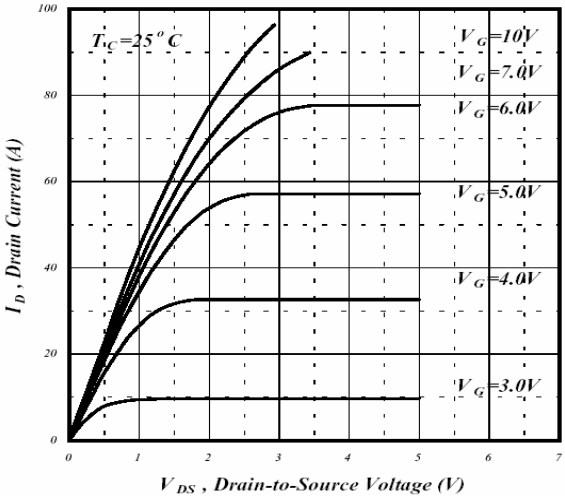


Fig 1. Typical Output Characteristics

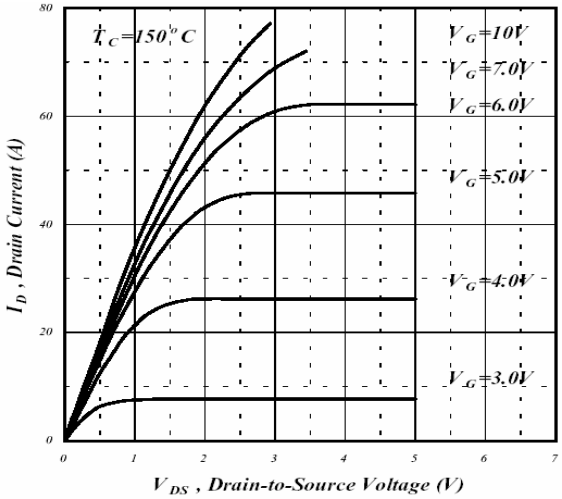


Fig 2. Typical Output Characteristics

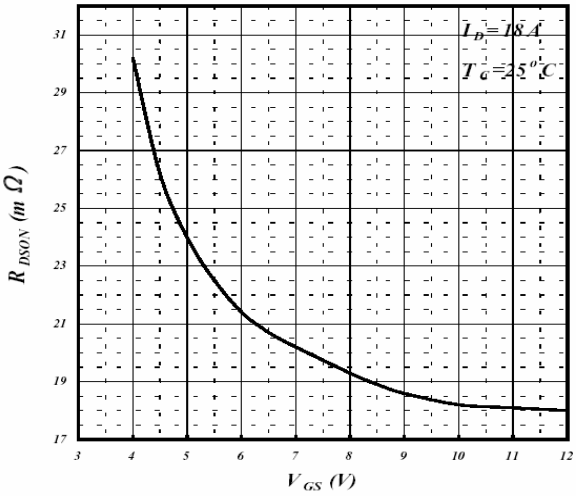


Fig 3. On-Resistance v.s. Gate Voltage

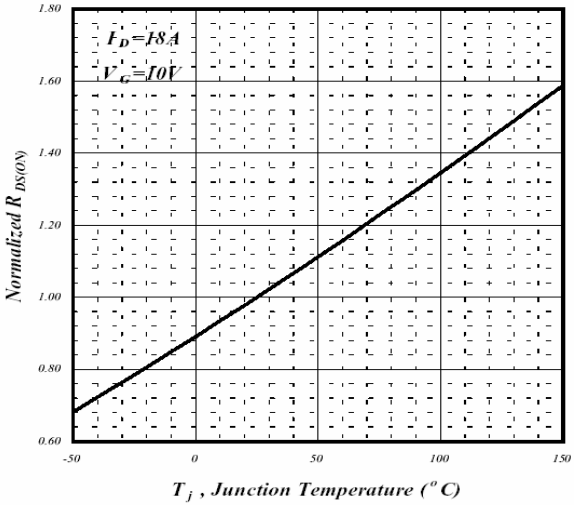


Fig 4. Normalized On-Resistance v.s. Junction Temperature

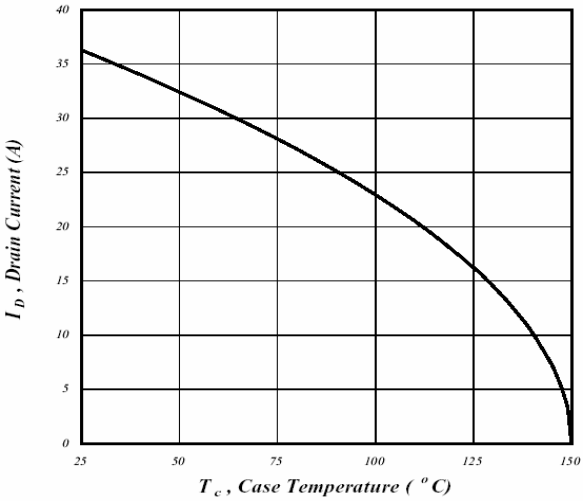


Fig 5. Maximum Drain Current v.s. Case Temperature

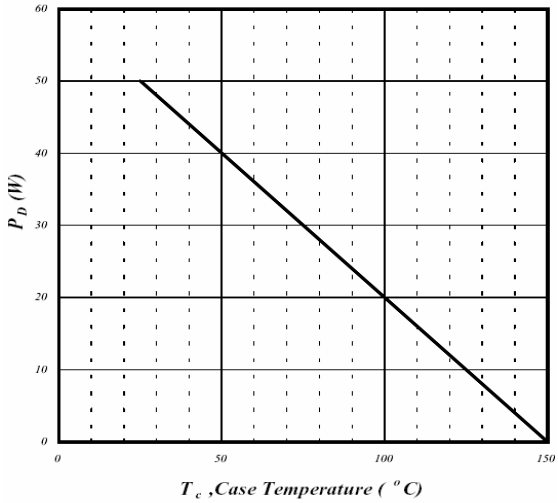


Fig 6. Type Power Dissipation

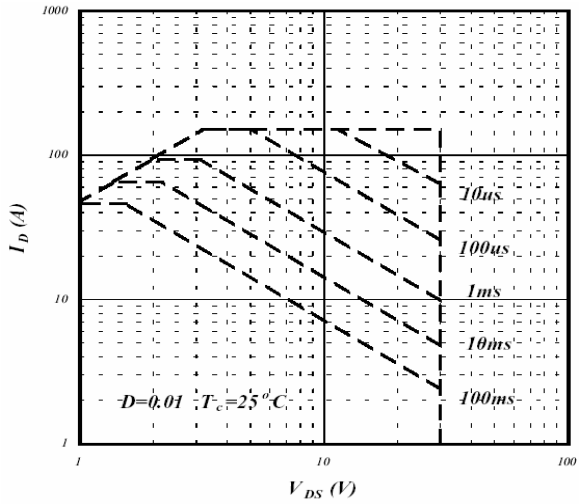


Fig 7. Maximum Safe Operating Area

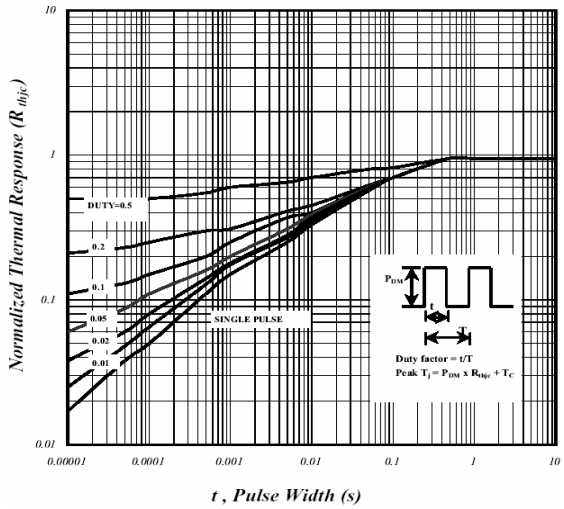


Fig 8. Effective Transient Thermal Impedance

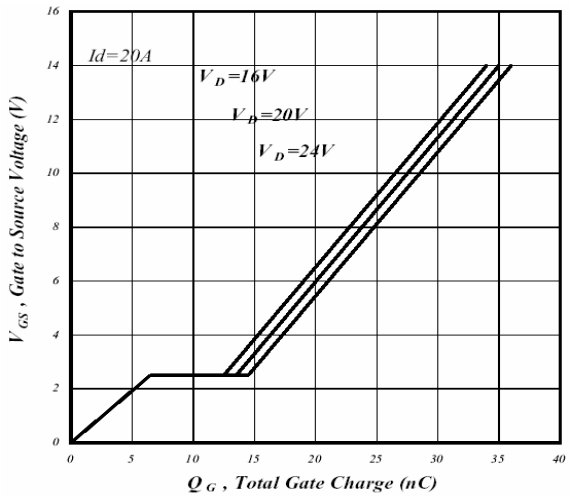


Fig 9. Gate Charge Characteristics

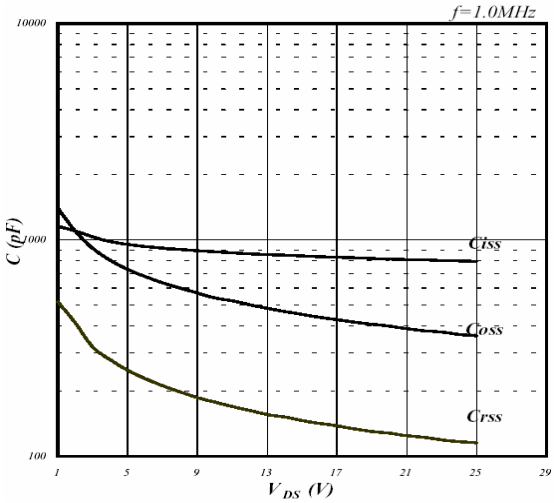


Fig 10. Typical Capacitance Characteristics

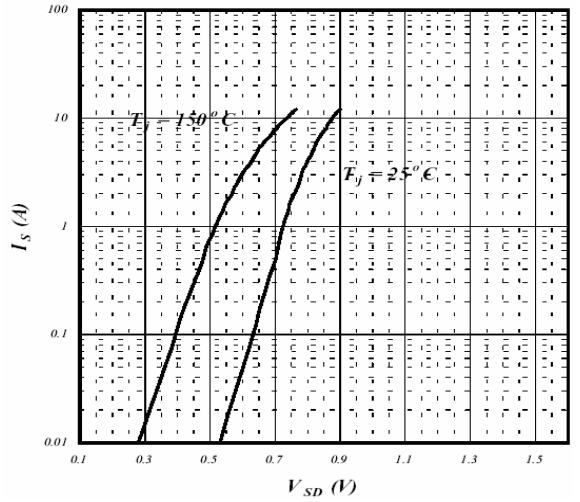


Fig 11. Forward Characteristics of Reverse Diode

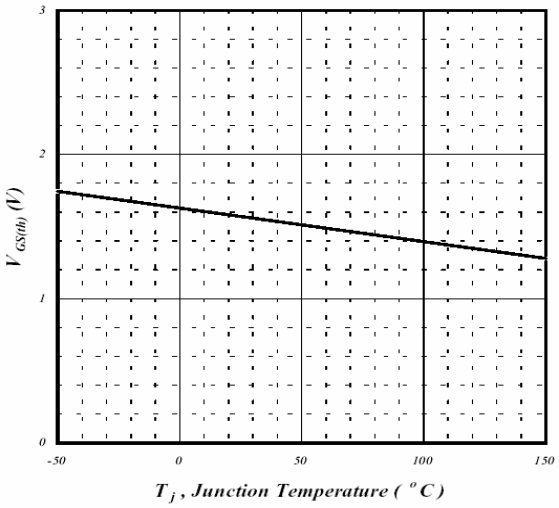


Fig 12. Gate Threshold Voltage v.s. Junction Temperature

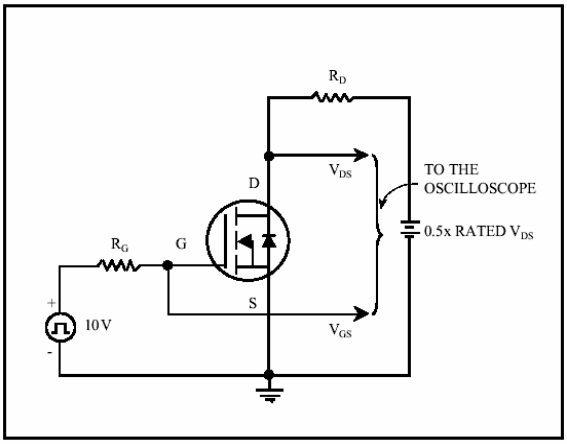


Fig 13. Switching Time Circuit

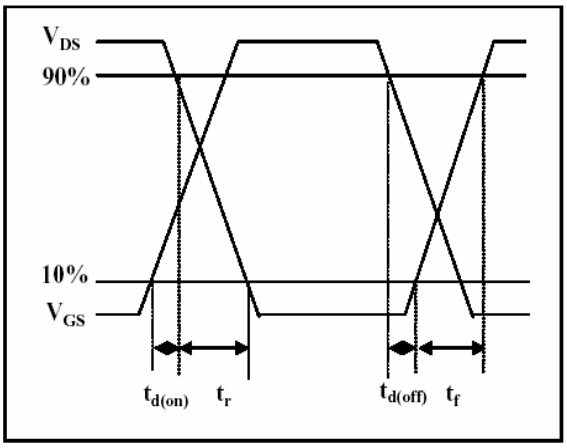


Fig 14. Switching Time Waveform

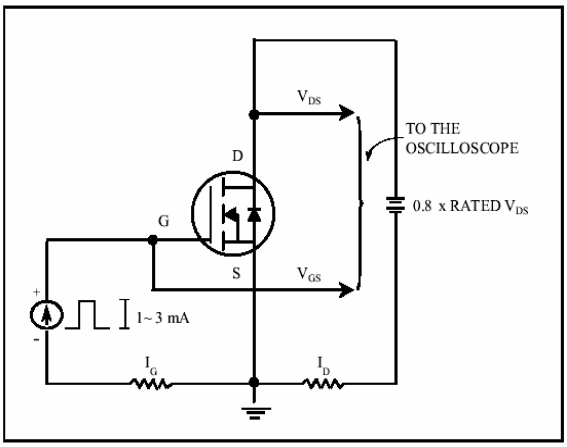


Fig 15. Gate Charge Circuit

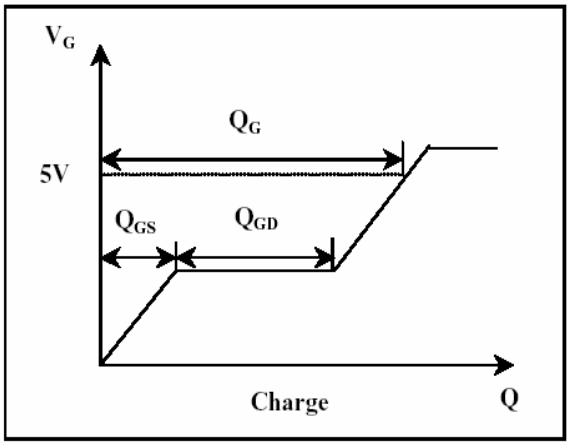


Fig 16. Gate Charge Waveform